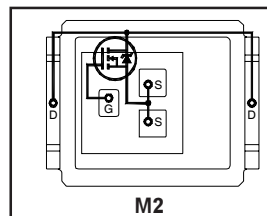


AUIRF7675M2TR AUIRF7675M2TR1

- Advanced Process Technology
- Optimized for Class D Audio Amplifier Applications
- Low $R_{DS(on)}$ for Improved Efficiency
- Low Q_g for Better THD and Improved Efficiency
- Low Q_{rr} for Better THD and Lower EMI
- Low Parasitic Inductance for Reduced Ringing and Lower EMI
- Delivers up to 250W per Channel into 4Ω with No Heatsink
- Dual Sided Cooling
- 175°C Operating Temperature
- Repetitive Avalanche Capability for Robustness and Reliability
- Lead free, RoHS and Halogen free

DirectFET™ Power MOSFET ②

$V_{(BR)DSS}$	150V
$R_{DS(on)}$ typ.	47mΩ
	56mΩ
R_G (typical)	1.2Ω
Q_g (typical)	21nC



Applicable DirectFET Outline and Substrate Outline ①

SB	SC		M2	M4		L4	L6	L8	
----	----	--	-----------	----	--	----	----	----	--

Description

The AUIRF7675M2TR/TR1 combines the latest Automotive HEXFET® Power MOSFET Silicon technology with the advanced DirectFET packaging platform to produce a best in class part for Automotive Class D audio amplifier applications. The DirectFET package is compatible with existing layout geometries used in power applications, PCB assembly equipment and vapor phase, infra-red or convection soldering techniques, when application note AN-1035 is followed regarding the manufacturing methods and processes. The DirectFET package allows dual sided cooling to maximize thermal transfer in automotive power systems.

This HEXFET Power MOSFET optimizes gate charge, body diode reverse recovery and internal gate resistance to improve key Class D audio amplifier performance factors such as efficiency, THD and EMI. Moreover the DirectFET packaging platform offers low parasitic inductance and resistance when compared to conventional wire bonded SOIC packages which improves EMI performance by reducing the voltage ringing that accompanies current transients.

These features combine to make this MOSFET a highly desirable component in Automotive Class D audio amplifier systems.

Absolute Maximum Ratings

	Parameter	Max.	Units
V _{DS}	Drain-to-Source Voltage	150	V
V _{GS}	Gate-to-Source Voltage	± 20	
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V (Silicon Limited)④	18	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V (Silicon Limited)④	13	
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V (Silicon Limited)③	4.4	
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V (Package Limited)	90	
I _{DM}	Pulsed Drain Current ④	72	
P _D @T _C = 25°C	Power Dissipation ④	45	W
P _D @T _A = 25°C	Power Dissipation ③	2.7	
E _{AS}	Single Pulse Avalanche Energy (Thermally Limited) ②	59	mJ
E _{AS} (tested)	Single Pulse Avalanche Energy Tested Value ⑤	170	
I _{AR}	Avalanche Current ①	See Fig.18a, 18b, 15, 16	A
E _{AR}	Repetitive Avalanche Energy ①		mJ
T _P	Peak Soldering Temperature	270	°C
T _J	Operating Junction and	-55 to + 175	
T _{STG}	Storage Temperature Range		

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ③	—	60	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction-to-Ambient ③	12.5	—	
$R_{\theta JA}$	Junction-to-Ambient ⑨	20	—	
$R_{\theta J-Can}$	Junction-to-Can ④⑩	—	3.3	
$R_{\theta J-PCB}$	Junction-to-PCB Mounted	1.4	—	
	Linear Derating Factor ④⑩	0.3		W/ $^\circ\text{C}$

HEXFET® is a registered trademark of International Rectifier.

AUIRF7675M2TR/TR1

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

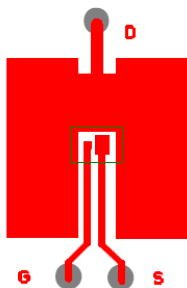
	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	150	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.16	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	47	56	m Ω	$V_{GS} = 10V, I_D = 11A$ ⑦
$V_{GS(th)}$	Gate Threshold Voltage	3.0	4.0	5.0	V	$V_{DS} = V_{GS}, I_D = 100\mu A$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-11	—	mV/ $^\circ\text{C}$	
g_{fs}	Forward Transconductance	16	—	—	S	$V_{DS} = 50V, I_D = 11A$
R_G	Gate Resistance	—	1.2	5.0	Ω	
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 150V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 150V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$

Dynamic Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)

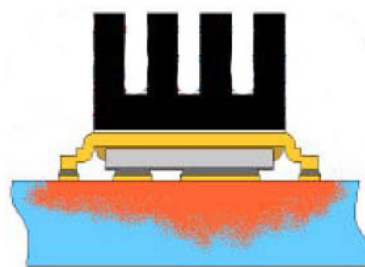
Q_g	Total Gate Charge	—	21	32	nC	$V_{DS} = 75V$ $V_{GS} = 10V$ $I_D = 11A$ See Fig. 6 and 17
Q_{gs1}	Pre-Vth Gate-to-Source Charge	—	5.2	—		
Q_{gs2}	Post-Vth Gate-to-Source Charge	—	1.6	—		
Q_{gd}	Gate-to-Drain Charge	—	7.1	—		
Q_{godr}	Gate Charge Overdrive	—	7.1	—		
Q_{sw}	Switch Charge ($Q_{gs2} + Q_{gd}$)	—	8.7	—	nC	$V_{DS} = 16V, V_{GS} = 0V$
Q_{oss}	Output Charge	—	8.8	—		
$t_{d(on)}$	Turn-On Delay Time	—	10	—	ns	$V_{DD} = 75V, V_{GS} = 10V$ ⑦ $I_D = 11A$ $R_G = 6.8\Omega$
t_r	Rise Time	—	13	—		
$t_{d(off)}$	Turn-Off Delay Time	—	14	—		
t_f	Fall Time	—	7.5	—		
C_{iss}	Input Capacitance	—	1360	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0\text{MHz}$ $V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$ $V_{GS} = 0V, V_{DS} = 120V, f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	190	—		
C_{rss}	Reverse Transfer Capacitance	—	41	—		
C_{oss}	Output Capacitance	—	1210	—		
C_{oss}	Output Capacitance	—	92	—		

Diode Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)

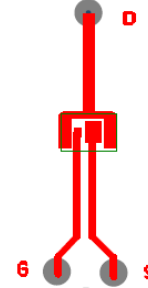
	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	18	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ⑤	—	—	72		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 11A, V_{GS} = 0V$ ⑦
t_{rr}	Reverse Recovery Time	—	63	95	ns	$T_J = 25^\circ\text{C}, I_F = 11A, V_{DD} = 25V$
Q_{rr}	Reverse Recovery Charge	—	180	270	nC	$di/dt = 100A/\mu s$ ⑦



③ Surface mounted on 1 in. square Cu (still air).



⑨ Mounted to a PCB with small clip heatsink (still air)



⑨ Mounted on minimum footprint full size board with metalized back and with small clip heatsink (still air)

Notes ① through ⑩ are on page 10

Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101) ^{††}	
		Comments: This product has passed an Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		SMALL CAN	MSL1, 260°C
ESD	Machine Model	Class M4 (+/-400V) AEC-Q101-002	
	Human Body Model	Class H1B (+/-1000V) AEC-Q101-001	
	Charged Device Model	Class HC4 (+/-1000V) AEC-Q101-005	
RoHS Compliant		Yes	

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com>

^{††} Exceptions to AEC-Q101 requirements are noted in the qualification report.

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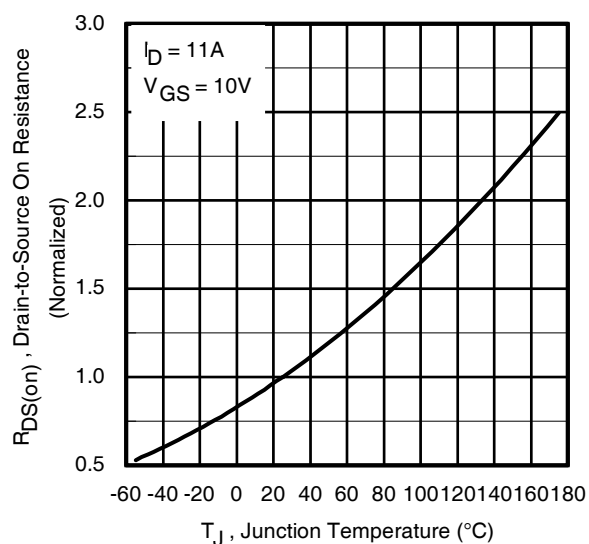
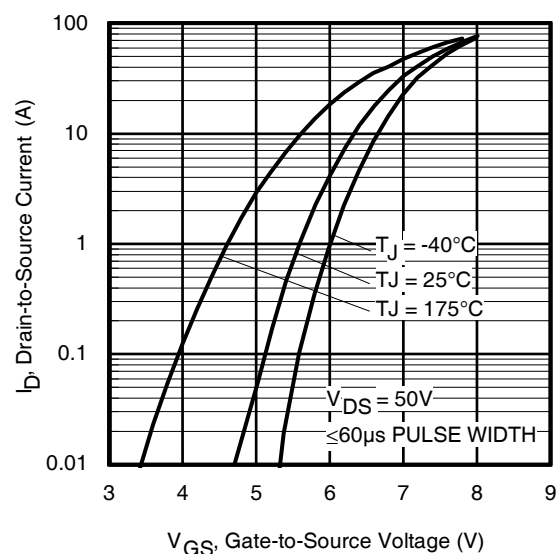
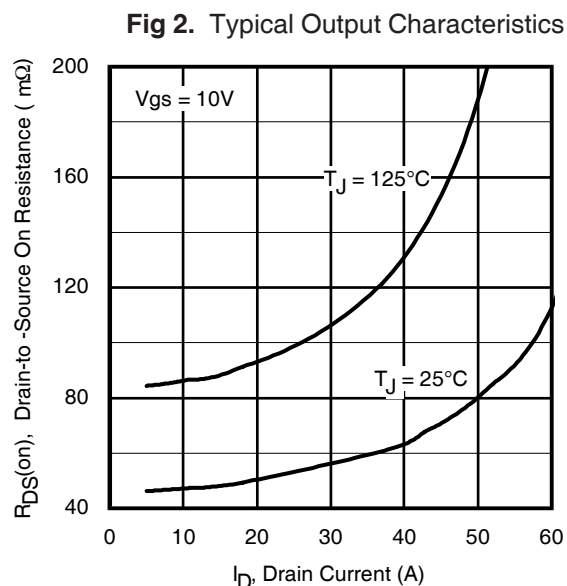
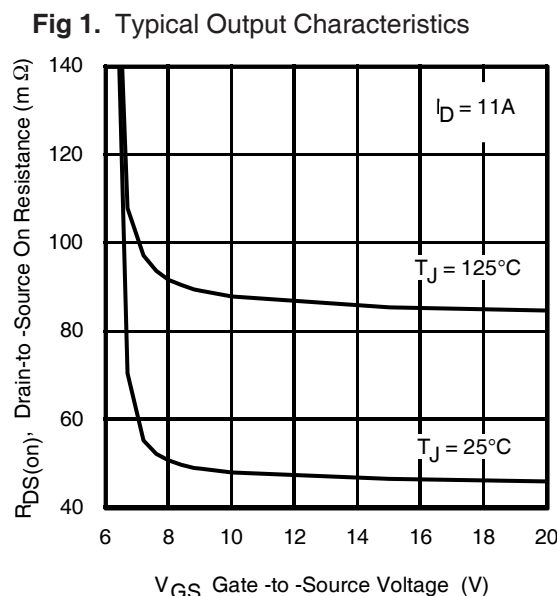
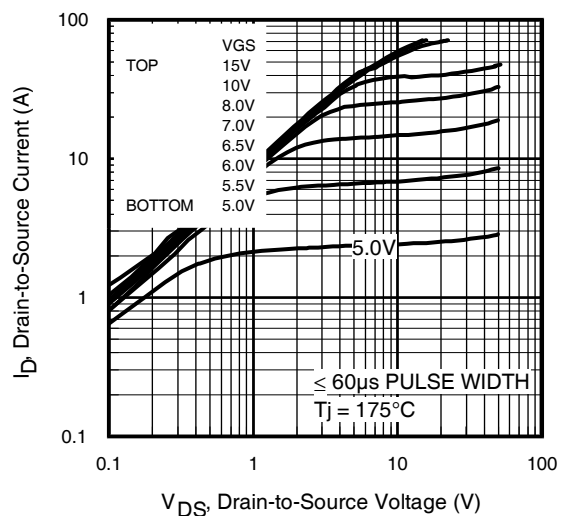
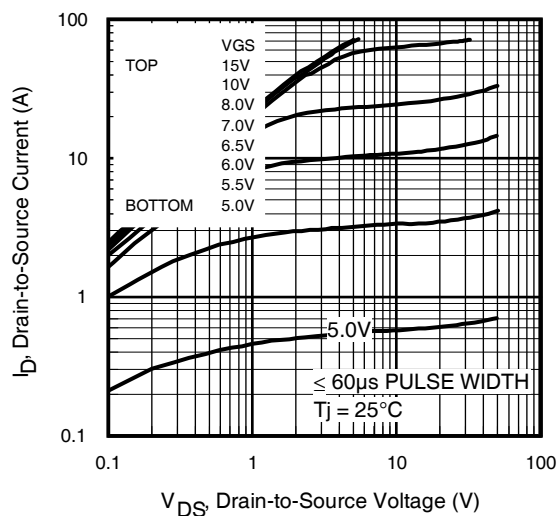


Fig 5. Typical Transfer Characteristics

Fig 6. Normalized On-Resistance vs. Temperature

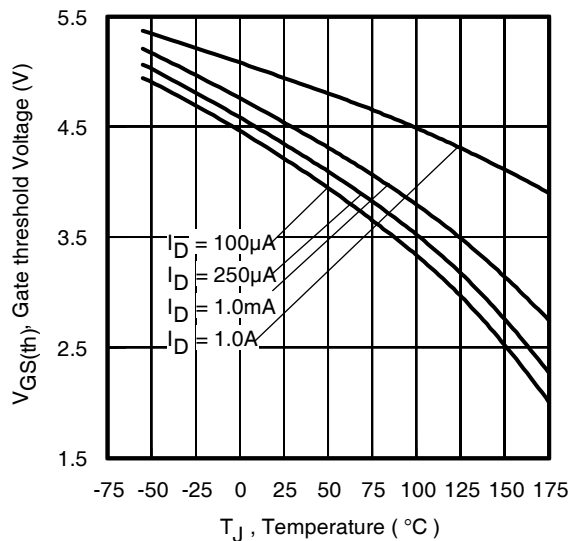


Fig 7. Typical Threshold Voltage vs. Junction Temperature

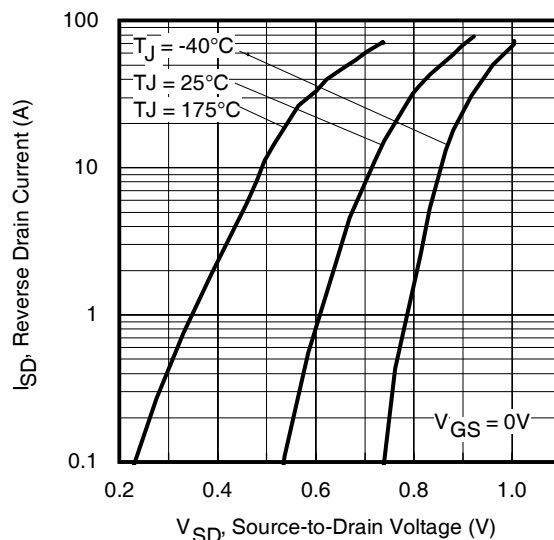


Fig 8. Typical Source-Drain Diode Forward Voltage

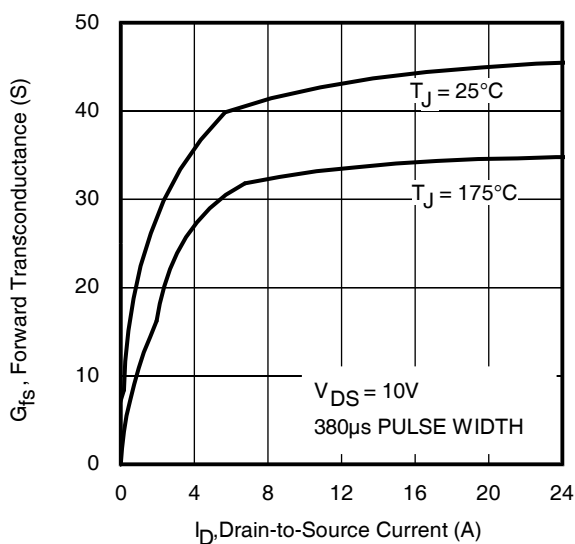


Fig 9. Typical Forward Transconductance Vs. Drain Current

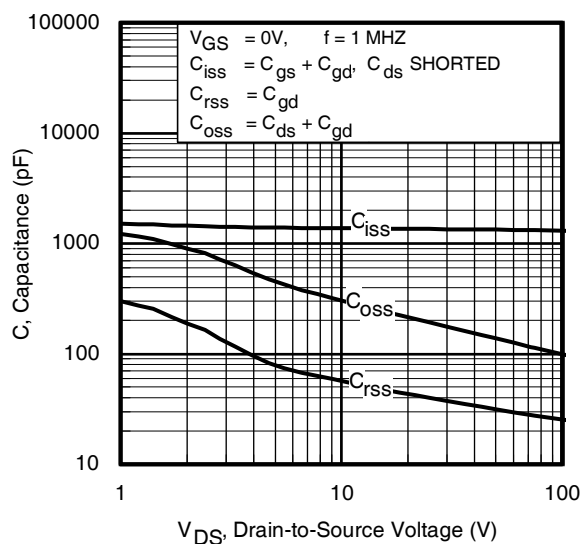


Fig 10. Typical Capacitance vs. Drain-to-Source Voltage

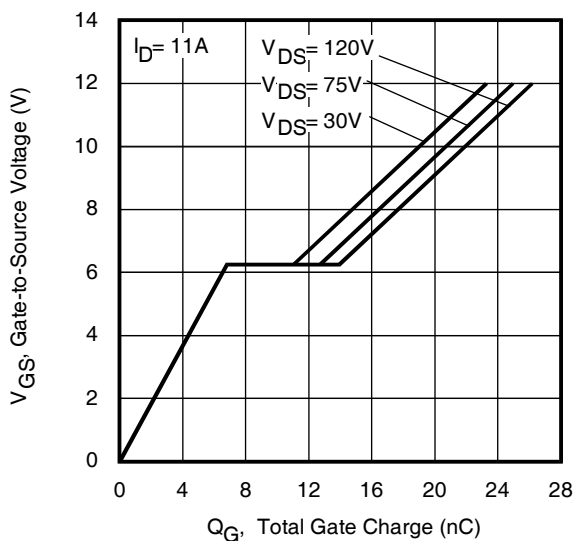
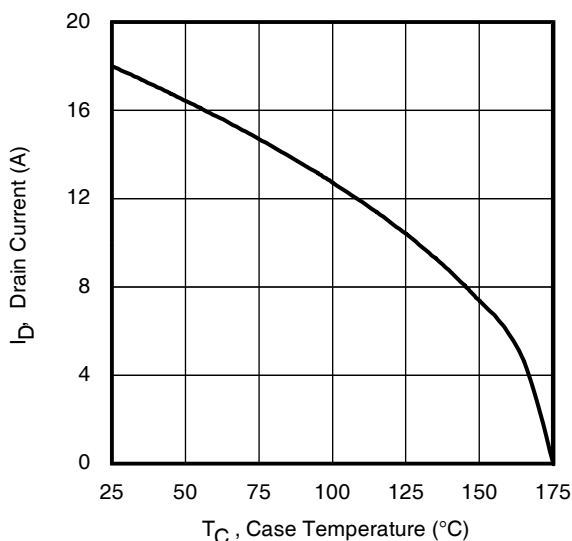
Fig.11 Typical Gate Charge vs. Gate-to-Source Voltage
www.irf.com

Fig 12. Maximum Drain Current vs. Case Temperature

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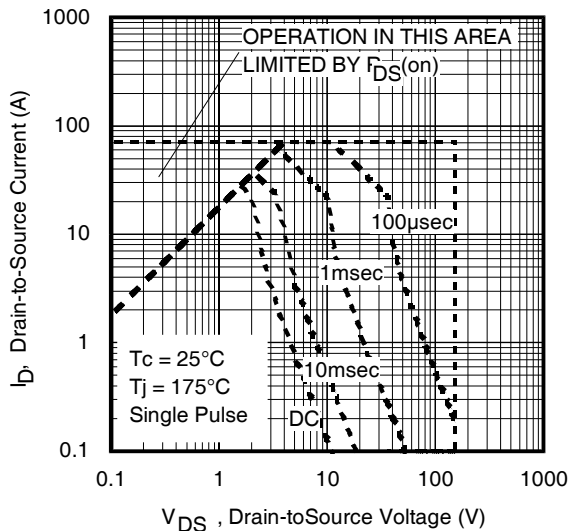


Fig 13. Maximum Safe Operating Area

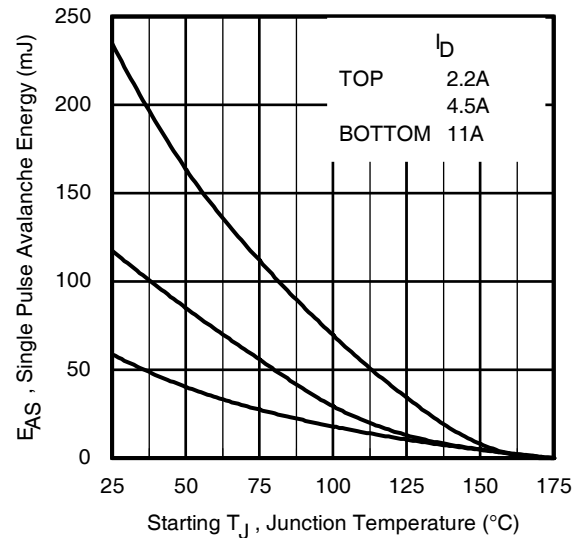


Fig 14. Maximum Avalanche Energy vs. Temperature

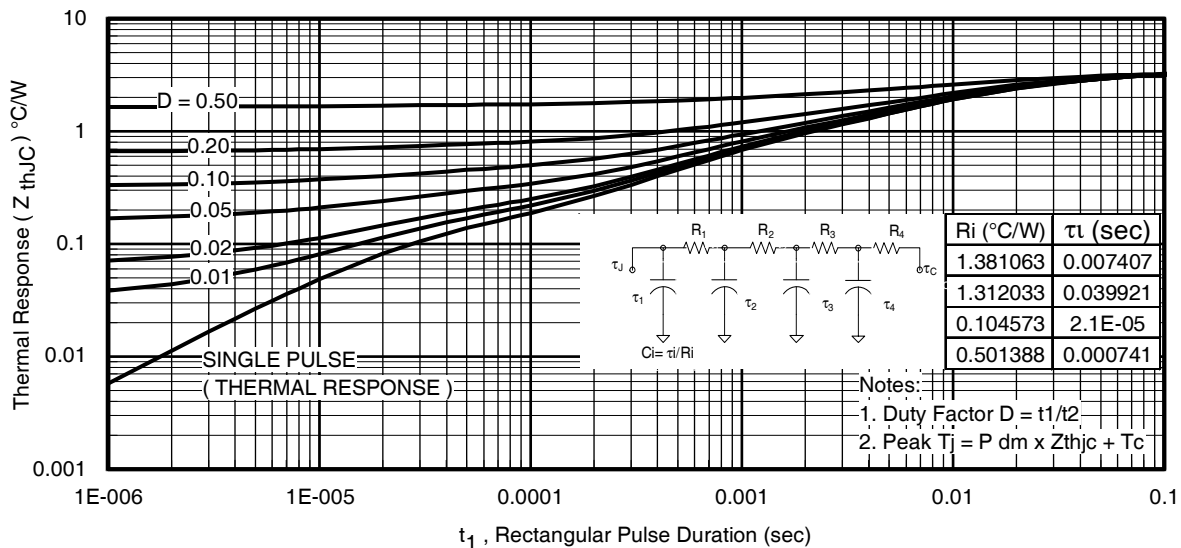


Fig 15. Maximum Effective Transient Thermal Impedance, Junction-to-Case

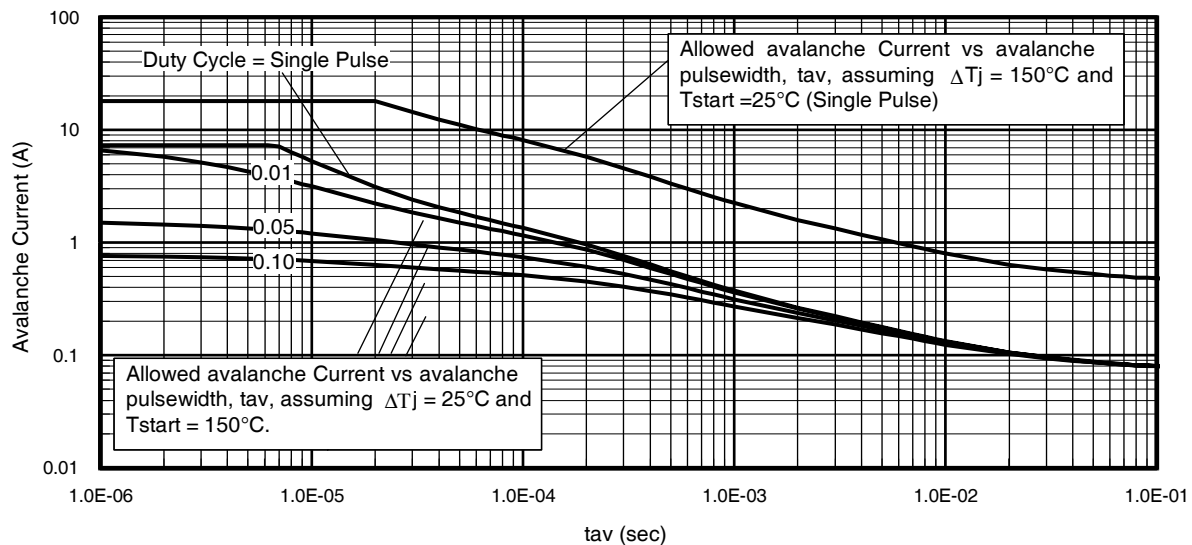


Fig 16. Typical Avalanche Current Vs. Pulsewidth

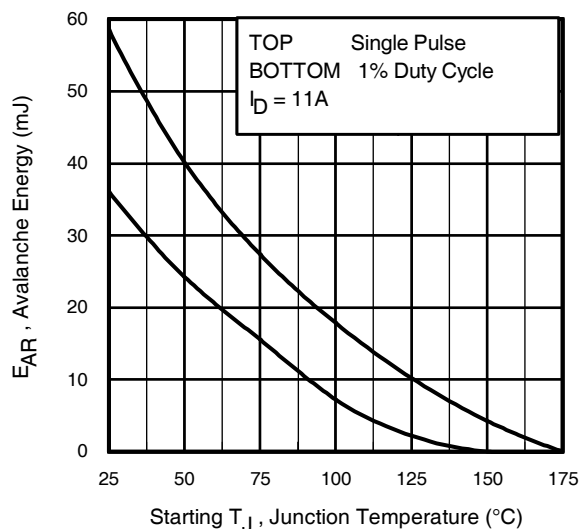


Fig 17. Maximum Avalanche Energy Vs. Temperature

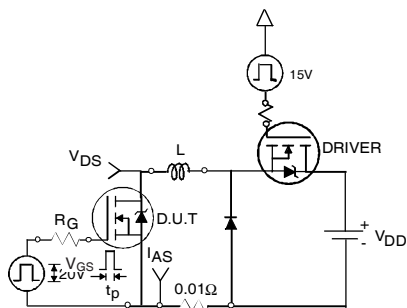


Fig 18a. Unclamped Inductive Test Circuit

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

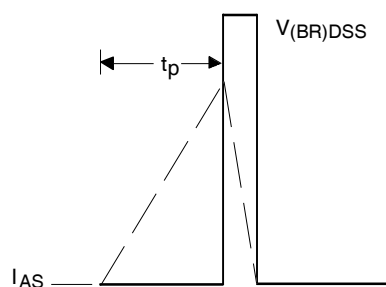


Fig 18b. Unclamped Inductive Waveforms

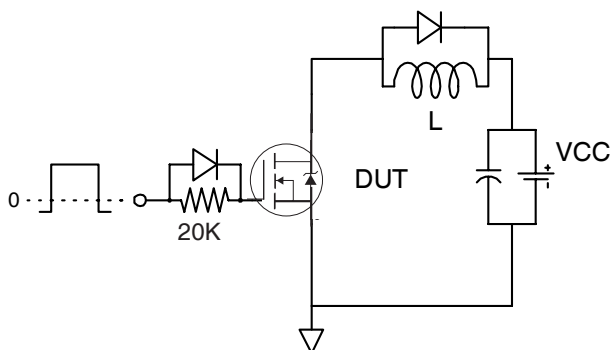


Fig 19a. Gate Charge Test Circuit

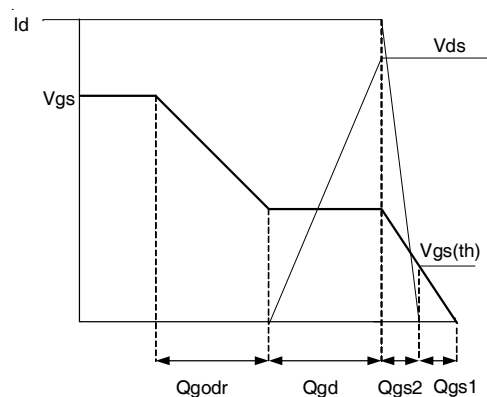


Fig 19b. Gate Charge Waveform

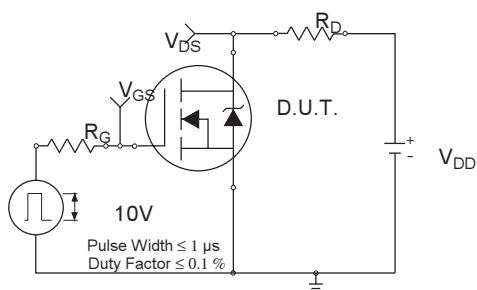


Fig 20a. Switching Time Test Circuit

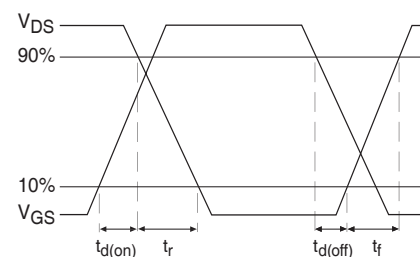


Fig 20b. Switching Time Waveforms

Notes on Repetitive Avalanche Curves , Figures 16, 17: (For further info, see AN-1005 at www.irf.com)

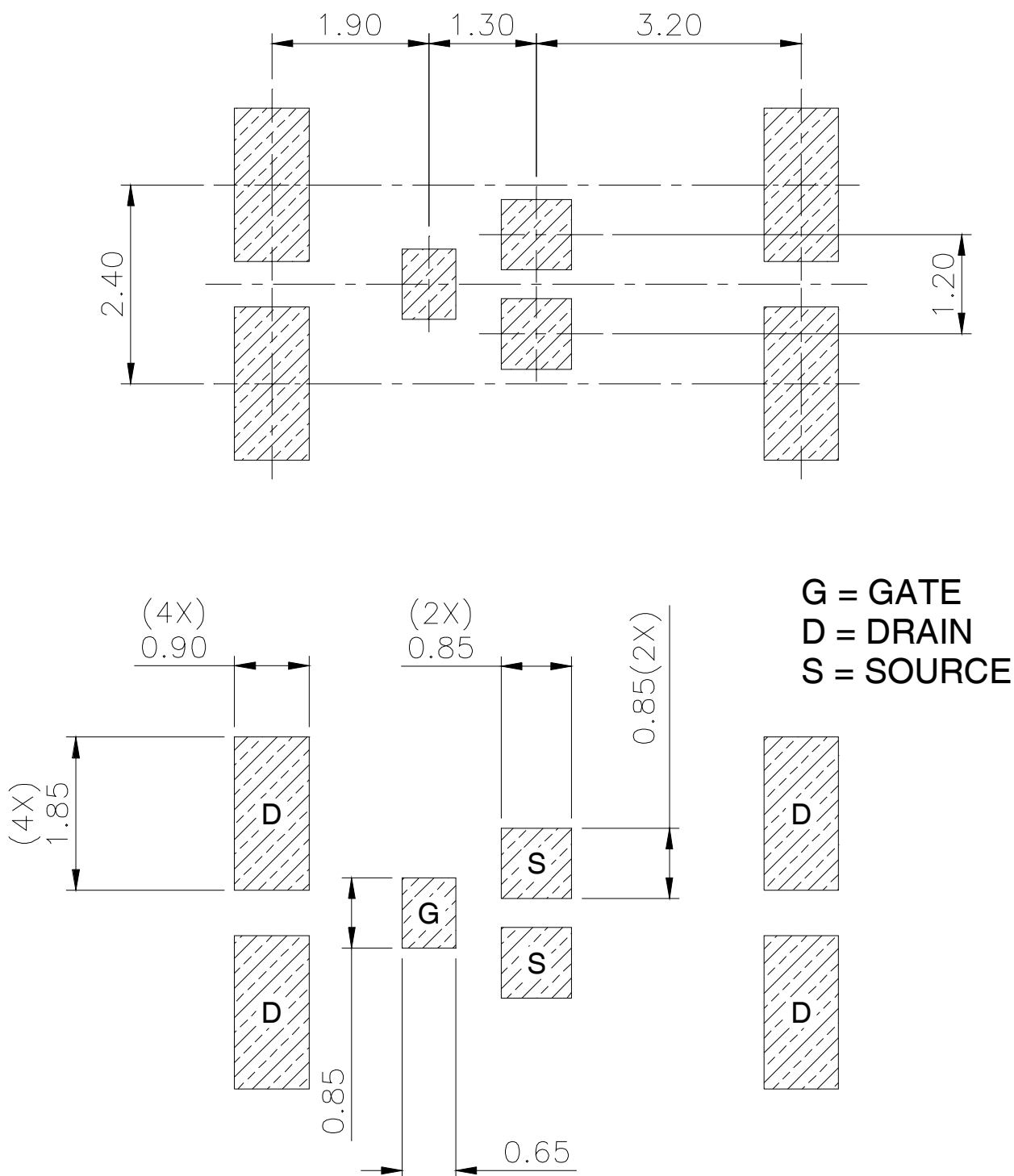
1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 18a, 18b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 16, 17).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see figure 11)

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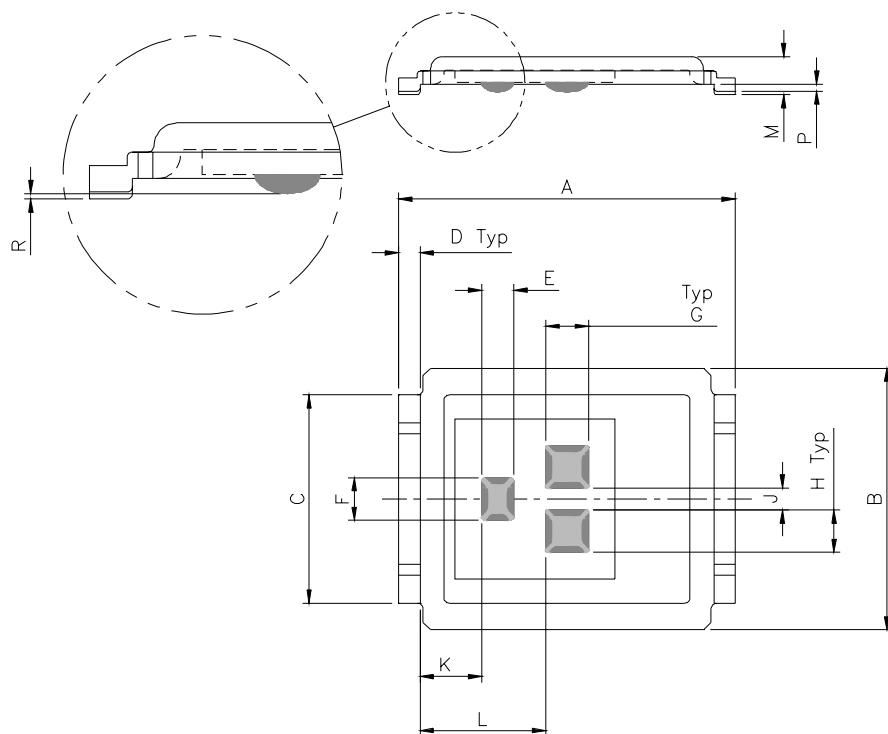
DirectFET™ Board Footprint, M2 (Medium Size Can).

Please see AN-1035 for DirectFET assembly details and stencil and substrate design recommendations

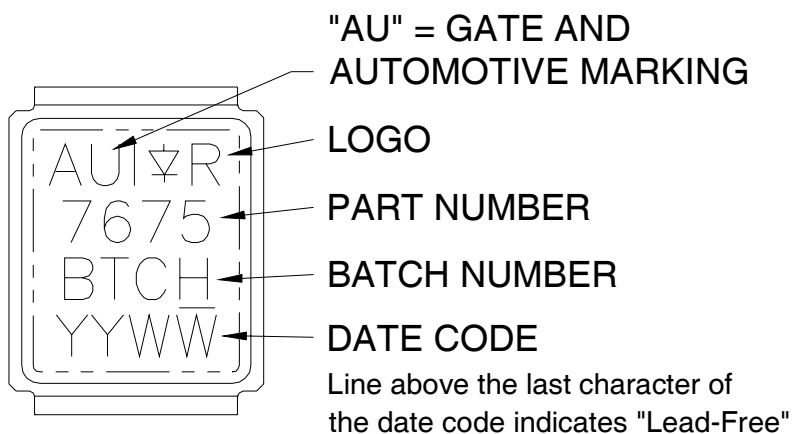


DirectFET™ Outline Dimension, M2 Outline (Medium Size Can).

Please see AN-1035 for DirectFET assembly details and stencil and substrate design recommendations



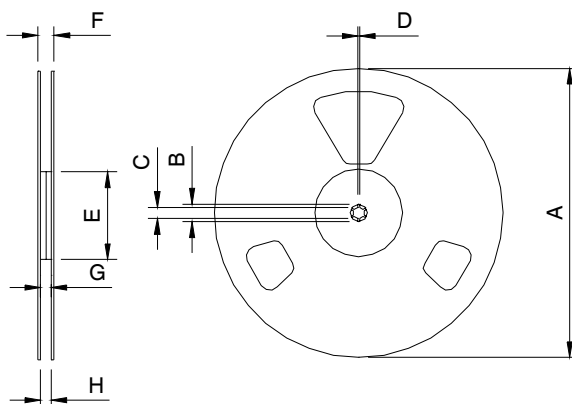
CODE	METRIC		IMPERIAL	
	MIN	MAX	MIN	MAX
A	6.25	6.35	0.246	0.250
B	4.80	5.05	0.189	0.201
C	3.85	3.95	0.152	0.156
D	0.35	0.45	0.014	0.018
E	0.58	0.62	0.023	0.024
F	0.78	0.82	0.031	0.032
G	0.78	0.82	0.031	0.032
H	0.78	0.82	0.031	0.032
I	N/A	N/A	N/A	N/A
J	0.38	0.42	0.015	0.017
K	1.10	1.20	0.043	0.047
L	2.30	2.40	0.090	0.094
M	0.68	0.74	0.027	0.029
P	0.09	0.17	0.003	0.007
R	0.02	0.08	0.001	0.003

DirectFET™ Part Marking

AUIRF7675M2TR/TR1

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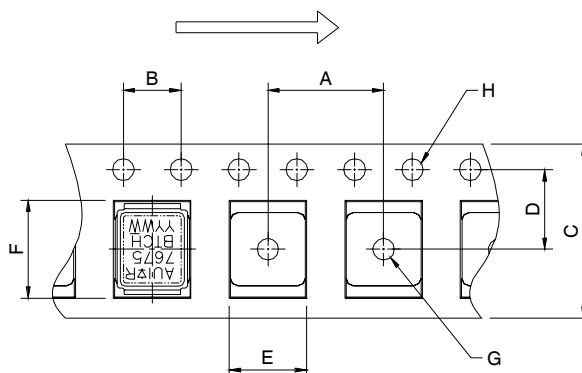
Automotive DirectFET™ Tape & Reel Dimension (Showing component orientation).



NOTE: Controlling dimensions in mm
Std reel quantity is 4800 parts. (ordered as AUIRF7675M2TR). For 1000 parts on 7" reel, order AUIRF7675M2TR1

REEL DIMENSIONS							
STANDARD OPTION (QTY 4800)				TR1 OPTION (QTY 1000)			
CODE	METRIC		IMPERIAL	MIN	METRIC		IMPERIAL
	MIN	MAX			MIN	MAX	
A	330.0	N.C	12.992		177.77	N.C	6.9
B	20.2	N.C	0.795		19.06	N.C	0.75
C	12.8	13.2	0.504		13.5	12.8	0.53
D	1.5	N.C	0.059		1.5	N.C	0.059
E	100.0	N.C	3.937		58.72	N.C	2.31
F	N.C	18.4	N.C		N.C	13.50	N.C
G	12.4	14.4	0.488		11.9	12.01	0.47
H	11.9	15.4	0.469		11.9	12.01	0.47

LOADED TAPE FEED DIRECTION



NOTE: CONTROLLING
DIMENSIONS IN MM

DIMENSIONS				
CODE	METRIC		IMPERIAL	
	MIN	MAX	MIN	MAX
A	7.90	8.10	0.311	0.319
B	3.90	4.10	0.154	0.161
C	11.90	12.30	0.469	0.484
D	5.45	5.55	0.215	0.219
E	5.10	5.30	0.201	0.209
F	6.50	6.70	0.256	0.264
G	1.50	N.C	0.059	N.C
H	1.50	1.60	0.059	0.063

Notes:

- Click on this section to link to the appropriate technical paper.
- Click on this section to link to the DirectFET Website.
- Surface mounted on 1 in. square Cu board, steady state.
- T_C measured with thermocouple mounted to top (Drain) of part.
- Repetitive rating; pulse width limited by max. junction temperature.
- Starting $T_J = 25^\circ\text{C}$, $L = 1.33\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 11\text{A}$.
- Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- Used double sided cooling, mounting pad with large heatsink.
- Mounted on minimum footprint full size board with metalized back and with small clip heatsink.
- R_θ is measured at T_J of approximately 90°C .

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IR warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with IR's standard warranty. Testing and other quality control techniques are used to the extent IR deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

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IR products are neither designed nor intended for use in automotive applications or environments unless the specific IR products are designated by IR as compliant with ISO/TS 16949 requirements and bear a part number including the designation "AU". Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, IR will not be responsible for any failure to meet such requirements

For technical support, please contact IR's Technical Assistance Center

<http://www.irf.com/technical-info/>

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233 Kansas St., El Segundo, California 90245

Tel: (310) 252-7105